MOCVD Workshop
Metal Organic Chemical Vapor Deposition: Growth, Application, and Analysis

12-4:30 pm April 5th, 2016
Paul G. Allen Bldg Annex, 101X Auditorium
Stanford University Campus

12:00-12:30pm: Refreshments and registration

12:30-12:40pm: Welcome. Prof. Roger T. Howe, Faculty Director of the Stanford Nanofabrication Facility and William E. Ayer Professor of Electrical Engineering.

12:40-1:10pm: MOCVD growth of III-V&III-N nanostructures, thin films and heterostructures. Dr. Xiaoqing Xu, Stanford Nanofabrication Facility, Stanford University

1:10-1:50pm: III-V on silicon for 300mm IC applications. Dr. Maxim Kelman, Sr. Technology Manager, AIXTRON SE.


2:30-3:00pm: Break

3:00-3:40pm: Implementation of DUV lasers for high Al content in GaN power devices and DUV LED’s and Yield optimization in LED manufacturing by introducing PL based defect control. Torsten Stoll, product marketing manager MCBU, Nanometrics Inc.

3:40-4:20pm: Non-contact Metrology for Compound Semiconductors. Dr. Mark Benjamin, Lehighton Electronics, Inc.

Register here or